

JRASET

International Journal for Research in Applied Science & Engineering Technology

IJRASET is indexed with Crossref for DOI-DOI: 10.22214

Website: www.ijraset.com, E-mail: ijraset@gmail.com



It is here by certified that the paper ID: IJRASET13062, entitled

Device Performance Analysis of Graphene Nanoribbon Field-Effect Transistor with Rare-Earth Oxide (La2O3) Based High-k Gate Dielectric

by M. K. Bera

after review is found suitable and has been published in Volume 6, Issue I, January 2018

11

International Journal for Research in Applied Science &
Engineering Technology
(International Pear Reviewed and Referred Journal)

(International Peer Reviewed and Refereed Journal)
Good luck for your future endeavors



ISRA Journal Impact Factor: **7.429**









By were



JRASET!

International Journal for Research in Applied Science & Engineering Technology

IJRASET is indexed with Crossref for DOI-DOI: 10.22214

Website: www.ijraset.com, E-mail: ijraset@gmail.com



It is here by certified that the paper ID: IJRASET13062, entitled

Device Performance Analysis of Graphene Nanoribbon Field-Effect Transistor with Rare-Earth Oxide (La2O3) Based High-k Gate Dielectric

by
S. P. Pandey

after review is found suitable and has been published in Volume 6, Issue I, January 2018

in

International Journal for Research in Applied Science & Engineering Technology

(International Peer Reviewed and Refereed Journal)
Good luck for your future endeavors



ISRA Journal Impact Factor: **7.429**









By were



JRASET

International Journal for Research in Applied Science & Engineering Technology

IJRASET is indexed with Crossref for DOI-DOI: 10.22214

Website: www.ijraset.com, E-mail: ijraset@gmail.com



It is here by certified that the paper ID: IJRASET13062, entitled

Device Performance Analysis of Graphene Nanoribbon Field-Effect Transistor with Rare-Earth Oxide (La2O3) Based High-k Gate Dielectric

by A. K. Sharma

after review is found suitable and has been published in Volume 6, Issue I, January 2018

in

International Journal for Research in Applied Science & Engineering Technology

(International Peer Reviewed and Refereed Journal)
Good luck for your future endeavors



ISRA Journal Impact Factor: **7.429**









By were



JRASET

International Journal for Research in Applied Science & Engineering Technology

IJRASET is indexed with Crossref for DOI-DOI: 10.22214

Website: www.ijraset.com, E-mail: ijraset@gmail.com



It is here by certified that the paper ID: IJRASET13062, entitled

Device Performance Analysis of Graphene Nanoribbon Field-Effect Transistor with Rare-Earth Oxide (La2O3) Based High-k Gate Dielectric

by D. K. Tyagi

after review is found suitable and has been published in Volume 6, Issue I, January 2018

in

International Journal for Research in Applied Science & Engineering Technology

(International Peer Reviewed and Refereed Journal)
Good luck for your future endeavors



ISRA Journal Impact Factor: **7.429**









By were



IJRASET

International Journal for Research in Applied Science & Engineering Technology

IJRASET is indexed with Crossref for DOI-DOI: 10.22214

Website: www.ijraset.com, E-mail: ijraset@gmail.com



It is here by certified that the paper ID: IJRASET13062, entitled

Device Performance Analysis of Graphene Nanoribbon Field-Effect Transistor with Rare-Earth Oxide (La2O3) Based High-k Gate Dielectric

by R. Mittal

after review is found suitable and has been published in Volume 6, Issue I, January 2018

in

International Journal for Research in Applied Science & Engineering Technology

(International Peer Reviewed and Refereed Journal)
Good luck for your future endeavors



ISRA Journal Impact Factor: **7.429**









By were